

N-channel 950 V, 3 Ω typ., 4 A Zener-protected SuperMESH3™ Power MOSFET in DPAK, TO-220FP, TO-220 and IPAK packages

Datasheet – production data

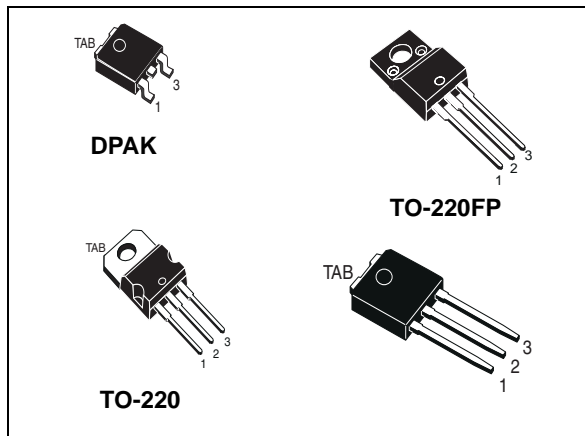
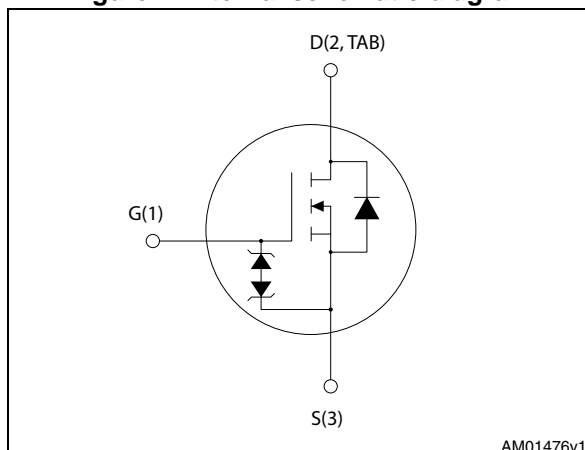


Figure 1. Internal schematic diagram



## Features

Order codes	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>	P <sub>TOT</sub>
STD5N95K3	950 V	3.5 Ω	4 A	90 W
STF5N95K3				25 W
STP5N95K3				90 W
STU5N95K3				90 W

- 100% avalanche tested
- Extremely large avalanche performance
- Gate charge minimized
- Very low intrinsic capacitances
- Zener-protected

## Applications

- Switching applications

## Description

These SuperMESH3™ Power MOSFETs are the result of improvements applied to STMicroelectronics' SuperMESH™ technology, combined with a new optimized vertical structure. These devices boast an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering them suitable for the most demanding applications.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STD5N95K3	5N95K3	DPAK	Tape and reel
STF5N95K3		TO-220FP	Tube
STP5N95K3		TO-220	
STU5N95K3		IPAK	

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value				Unit
		DPAK	TO-220FP	TO-220	IPAK	
$V_{GS}$	Gate- source voltage	±30				V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	4	4 <sup>(1)</sup>	4		A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	3	3 <sup>(1)</sup>	3		A
$I_{DM}^{(2)}$	Drain current (pulsed)	16	16 <sup>(1)</sup>	16		A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	90	25	90		W
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_J$ max)	4				A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	100				mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	5				V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ , $T_C = 25\text{ °C}$ )		2500			V
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 150				°C

1. Limited by maximum junction temperature
2. Pulse width limited by safe operating area
3.  $I_{SD} \leq 4\text{ A}$ ,  $di/dt \leq 100\text{ A}/\mu\text{s}$ , peak  $V_{DS} \leq V_{(BR)DSS}$

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		DPAK	TO-220FP	TO-220	IPAK	
$R_{thj-case}$	Thermal resistance junction-case max	1.39	5	1.39		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max		62.5		100	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50				°C/W

1. When mounted on 1inch² FR-4 board, 2 oz Cu

## 2 Electrical characteristics

(T<sub>case</sub> = 25 °C unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	950			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = 950 V V <sub>DS</sub> = 950 V, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			±10	μA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 100 μA	3	4	5	V
R <sub>DS(on)</sub>	Static drain-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A		3	3.5	Ω

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> = 25 V, f = 1 MHz, V <sub>GS</sub> = 0	-	460	-	pF
C <sub>oss</sub>	Output capacitance		-	38	-	pF
C <sub>rss</sub>	Reverse transfer capacitance		-	1	-	pF
C <sub>o(tr)</sub> <sup>(1)</sup>	Equivalent capacitance time related	V <sub>DS</sub> = 0 to 760 V, V <sub>GS</sub> = 0	-	970	-	pF
C <sub>o(er)</sub> <sup>(2)</sup>	Equivalent capacitance energy related	V <sub>DS</sub> = 0 to 760 V, V <sub>GS</sub> = 0	-	15	-	pF
R <sub>g</sub>	Gate input resistance	f = 1 MHz, I <sub>D</sub> = 0	-	5.5	-	Ω
Q <sub>g</sub>	Total gate charge	V <sub>DD</sub> = 760 V, I <sub>D</sub> = 4 A,	-	19	-	nC
Q <sub>gs</sub>	Gate-source charge	V <sub>GS</sub> = 10 V	-	4.7	-	nC
Q <sub>gd</sub>	Gate-drain charge	(see Figure 20)	-	12	-	nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 475\text{ V}$ , $I_D = 2\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 19)	-	17	-	ns
$t_r$	Rise time		-	7	-	ns
$t_{d(off)}$	Turn-off-delay time		-	32	-	ns
$t_f$	Fall time		-	18	-	ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		4	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		16	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 4\text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 4\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 21)	-	410		ns
$Q_{rr}$	Reverse recovery charge		-	3.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	17		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 4\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$ (see Figure 21)	-	516		ns
$Q_{rr}$	Reverse recovery charge		-	4.1		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	16		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 8. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0$	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for IPAK, DPAK

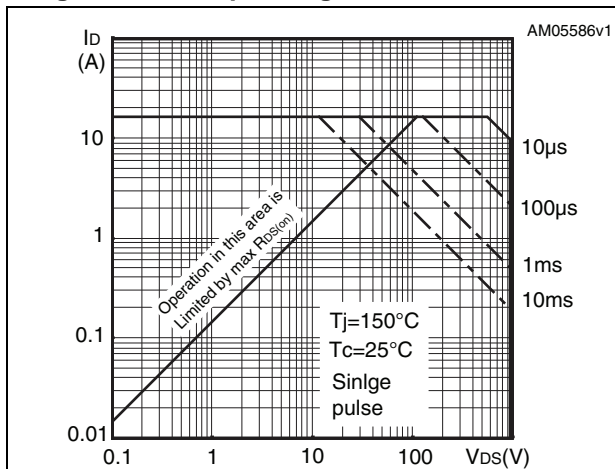


Figure 3. Thermal impedance for IPAK, DPAK

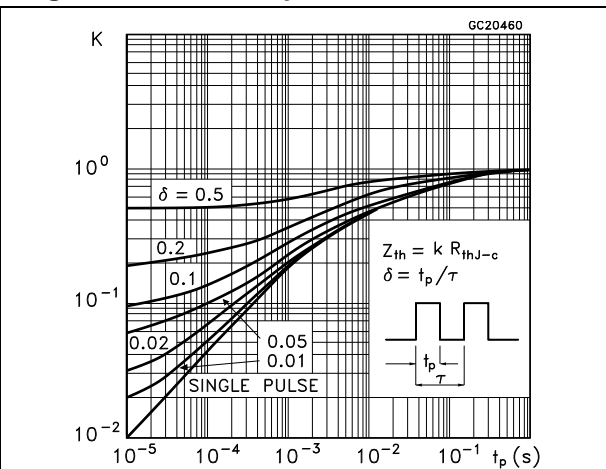


Figure 4. Safe operating area for TO-220FP

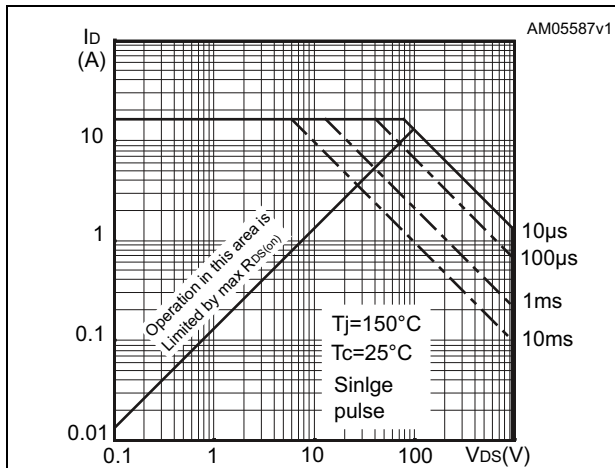


Figure 5. Thermal impedance for TO-220FP

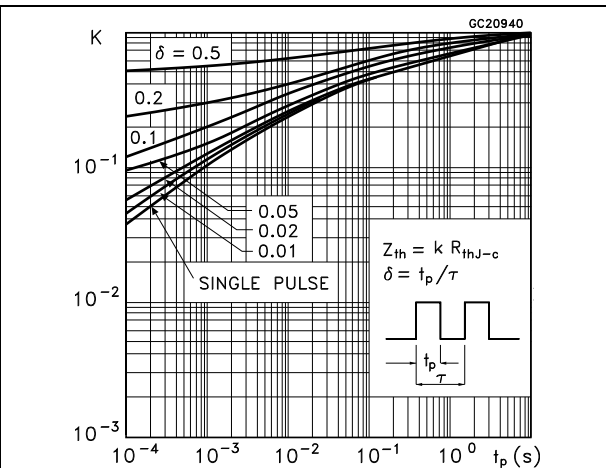


Figure 6. Safe operating area for TO-220

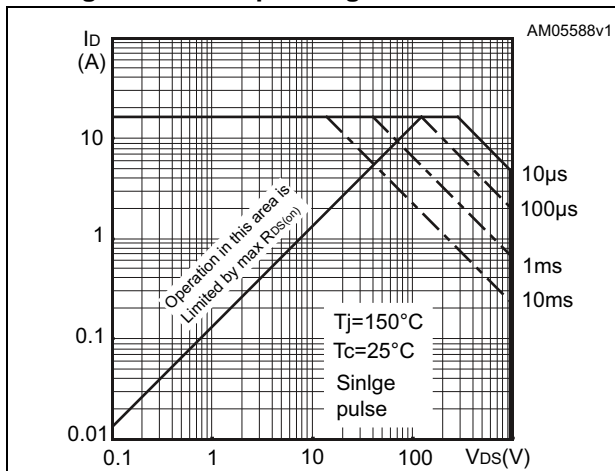


Figure 7. Thermal impedance for TO-220

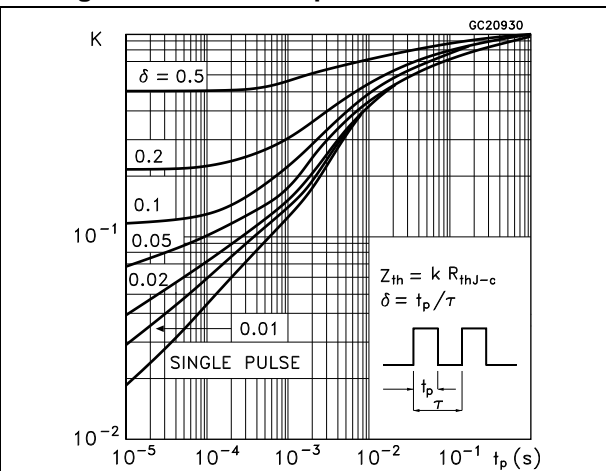


Figure 8. Output characteristics

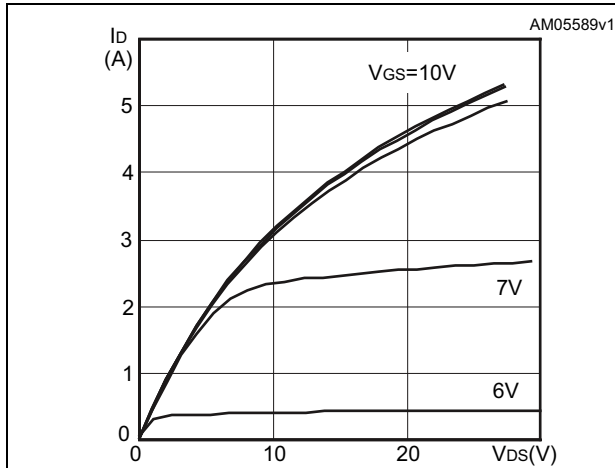


Figure 9. Transfer characteristics

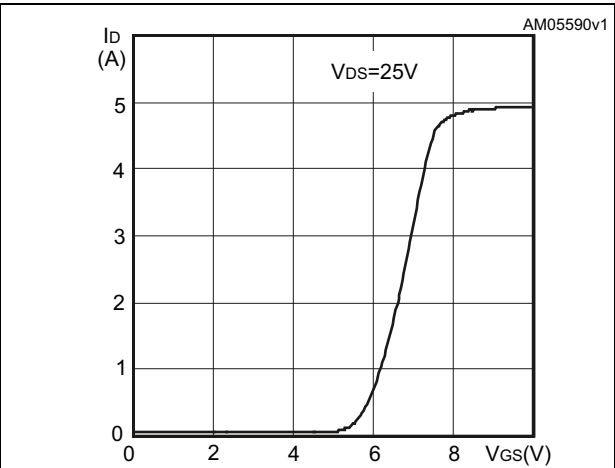


Figure 10. Gate charge vs gate-source voltage

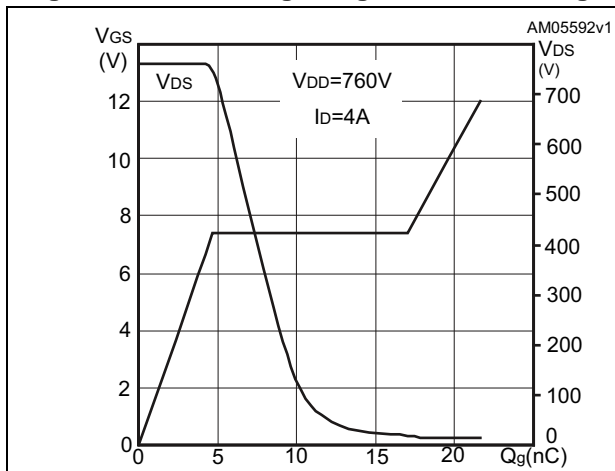


Figure 11. Static drain-source on-resistance

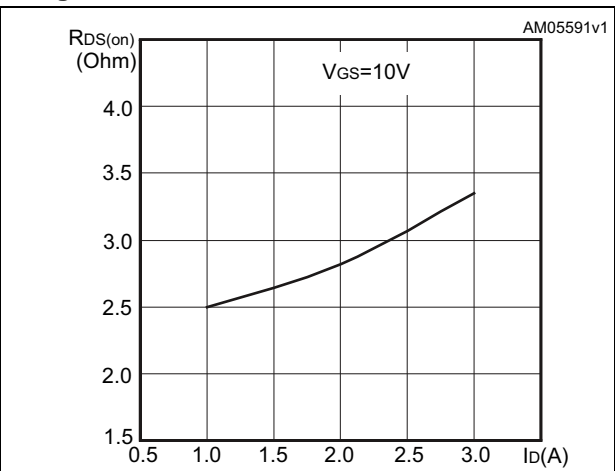


Figure 12. Capacitance variations

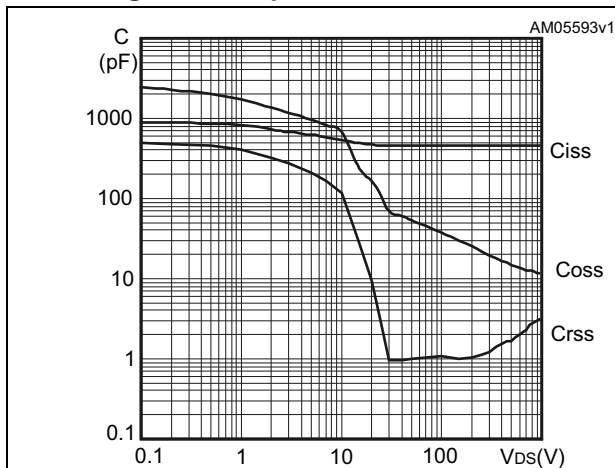


Figure 13. Output capacitance stored energy

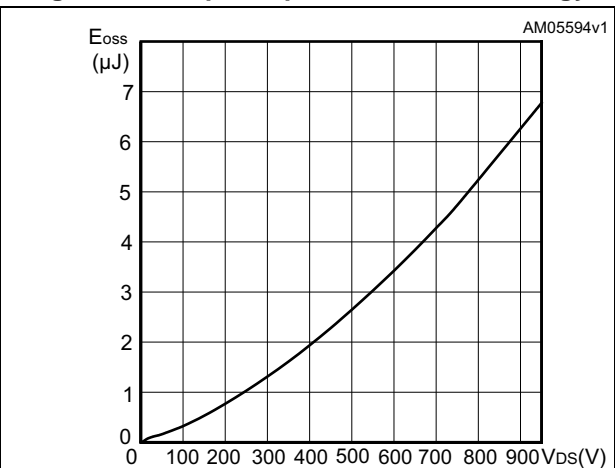


Figure 14. Normalized gate threshold voltage vs temperature

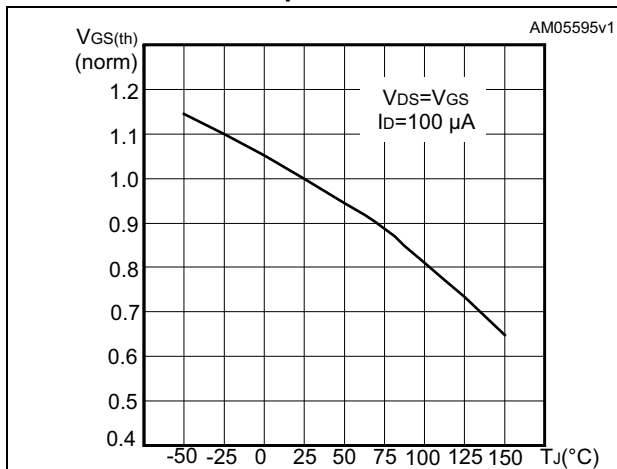


Figure 15. Normalized on-resistance vs temperature

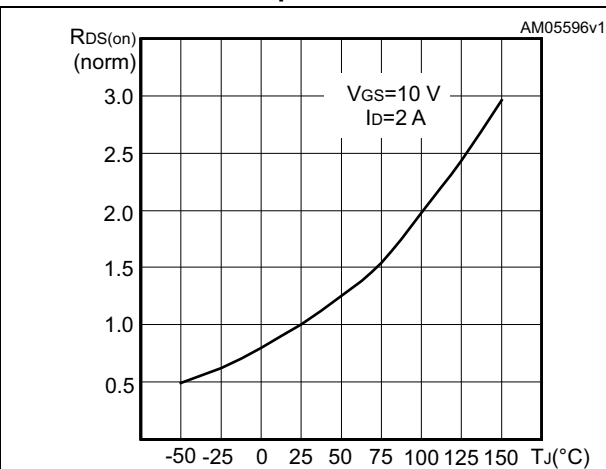


Figure 16. Source-drain diode forward characteristics

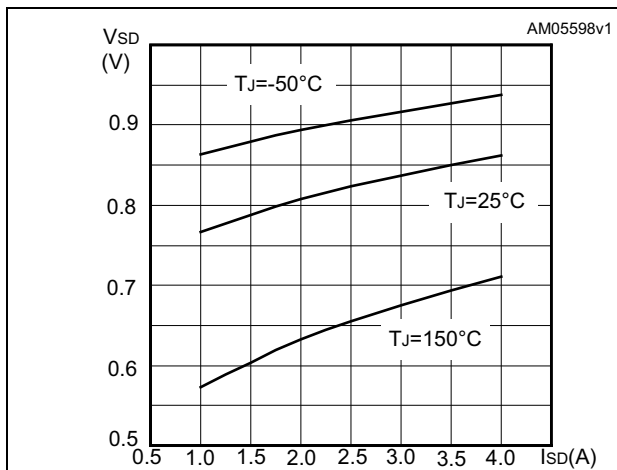


Figure 17. Normalized BV<sub>DSS</sub> vs temperature

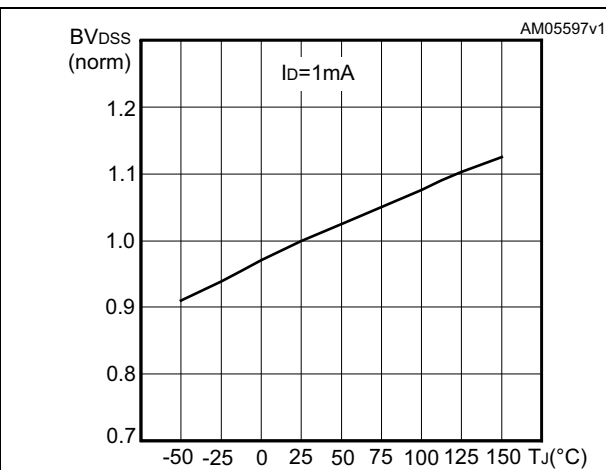
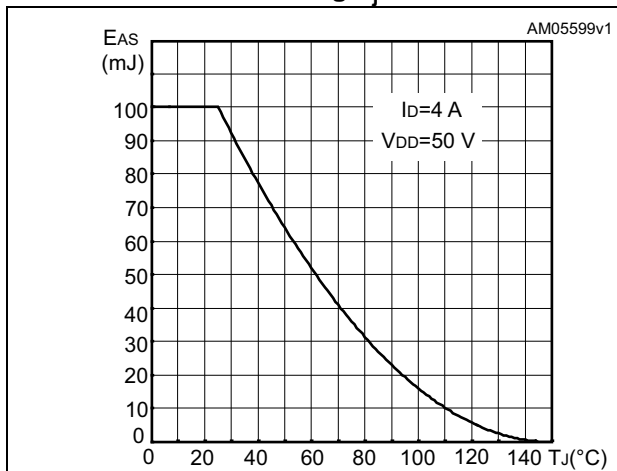


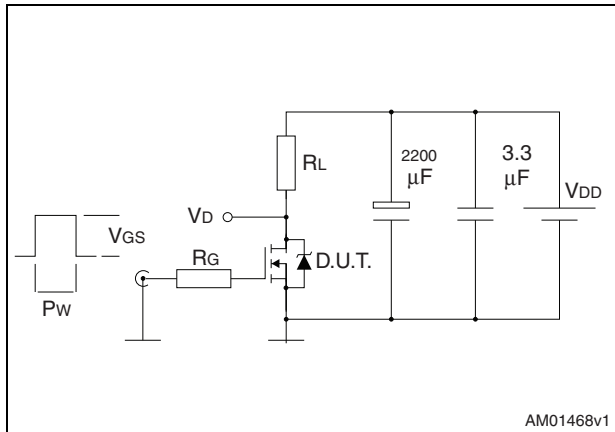
Figure 18. Maximum avalanche energy vs starting T<sub>j</sub>





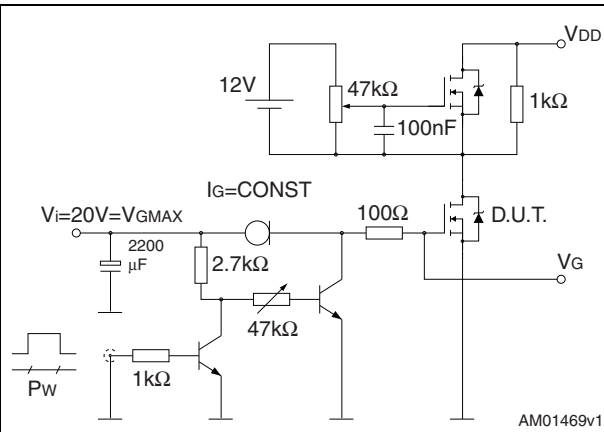
### 3 Test circuits

Figure 19. Switching times test circuit for resistive load



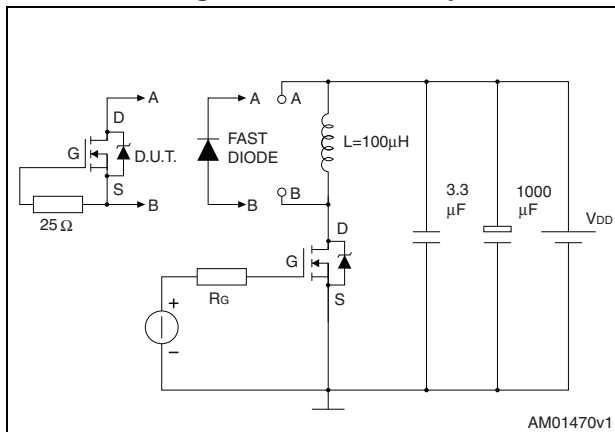
AM01468v1

Figure 20. Gate charge test circuit



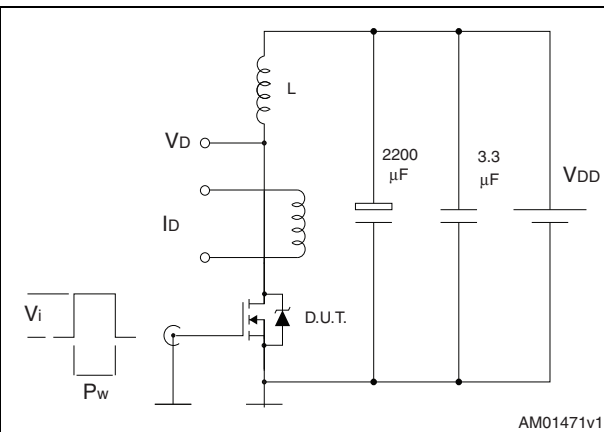
AM01469v1

Figure 21. Test circuit for inductive load switching and diode recovery times



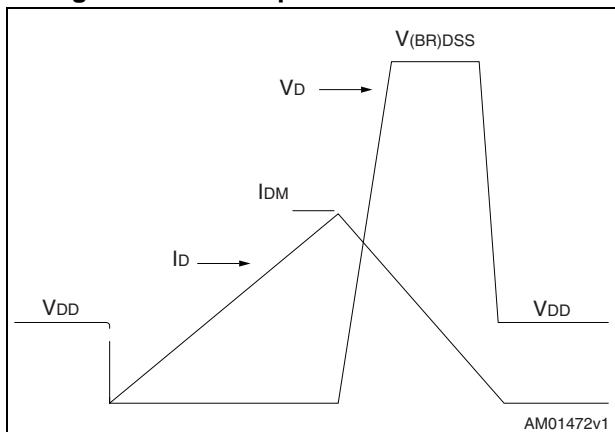
AM01470v1

Figure 22. Unclamped inductive load test circuit



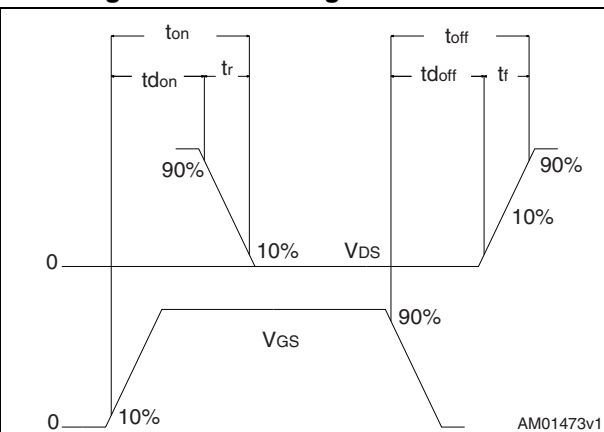
AM01471v1

Figure 23. Unclamped inductive waveform



AM01472v1

Figure 24. Switching time waveform



AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Table 9. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 25. DPAK (TO-252) drawing

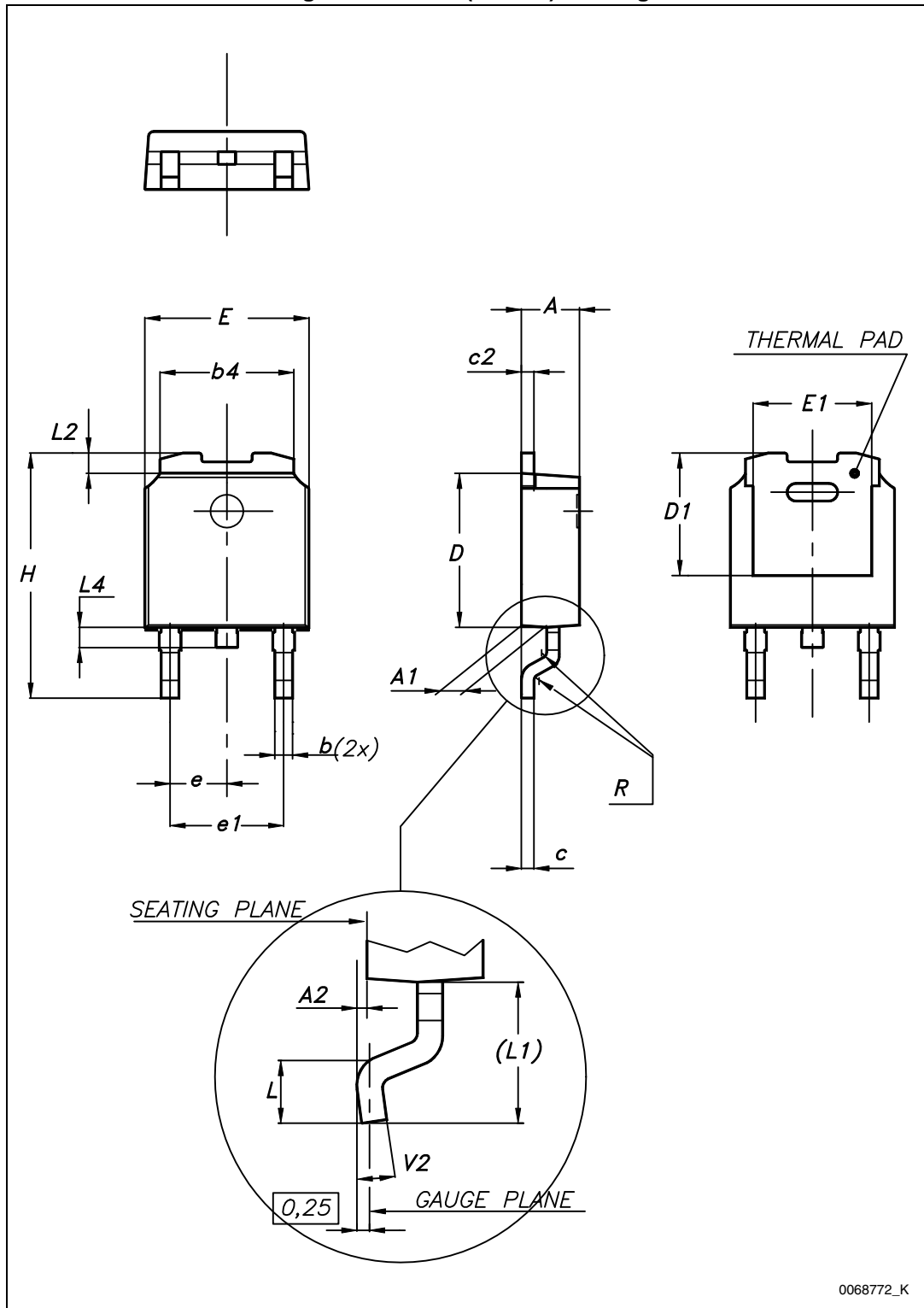
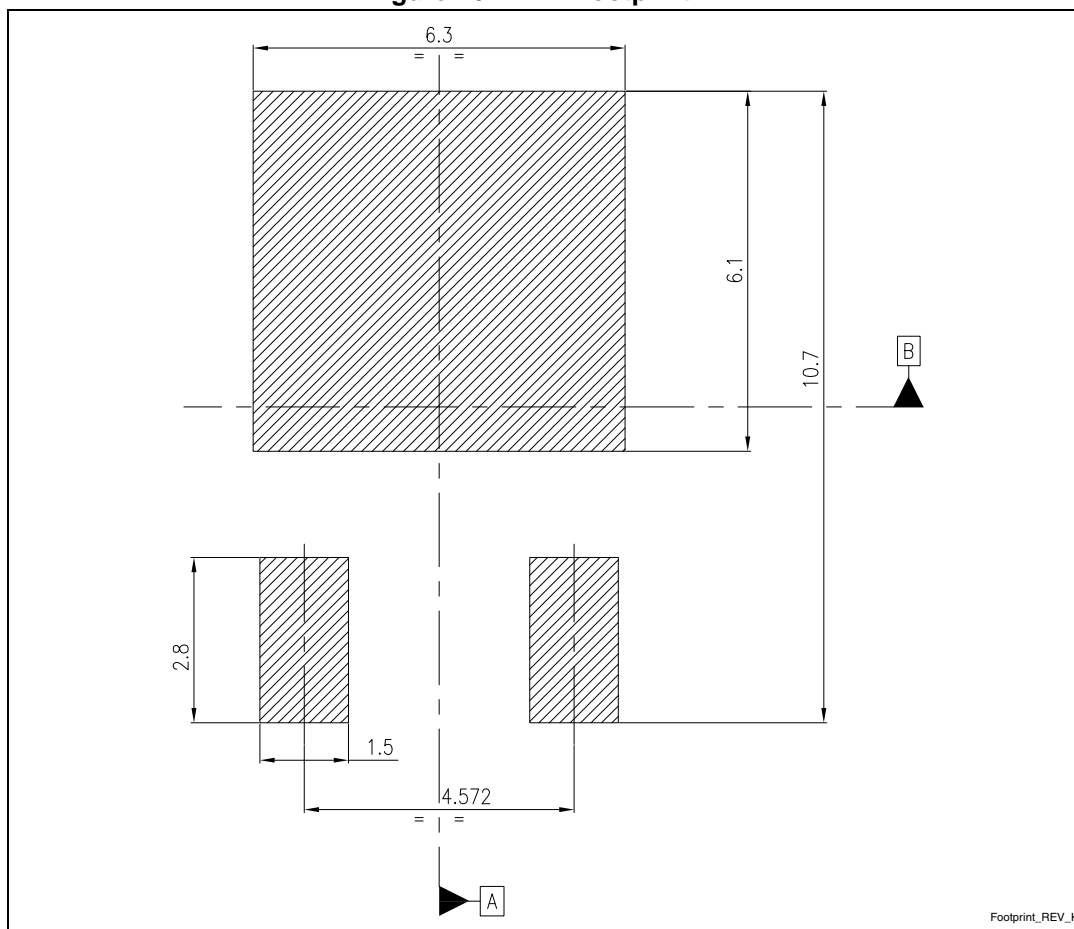


Figure 26. DPAK footprint (a)

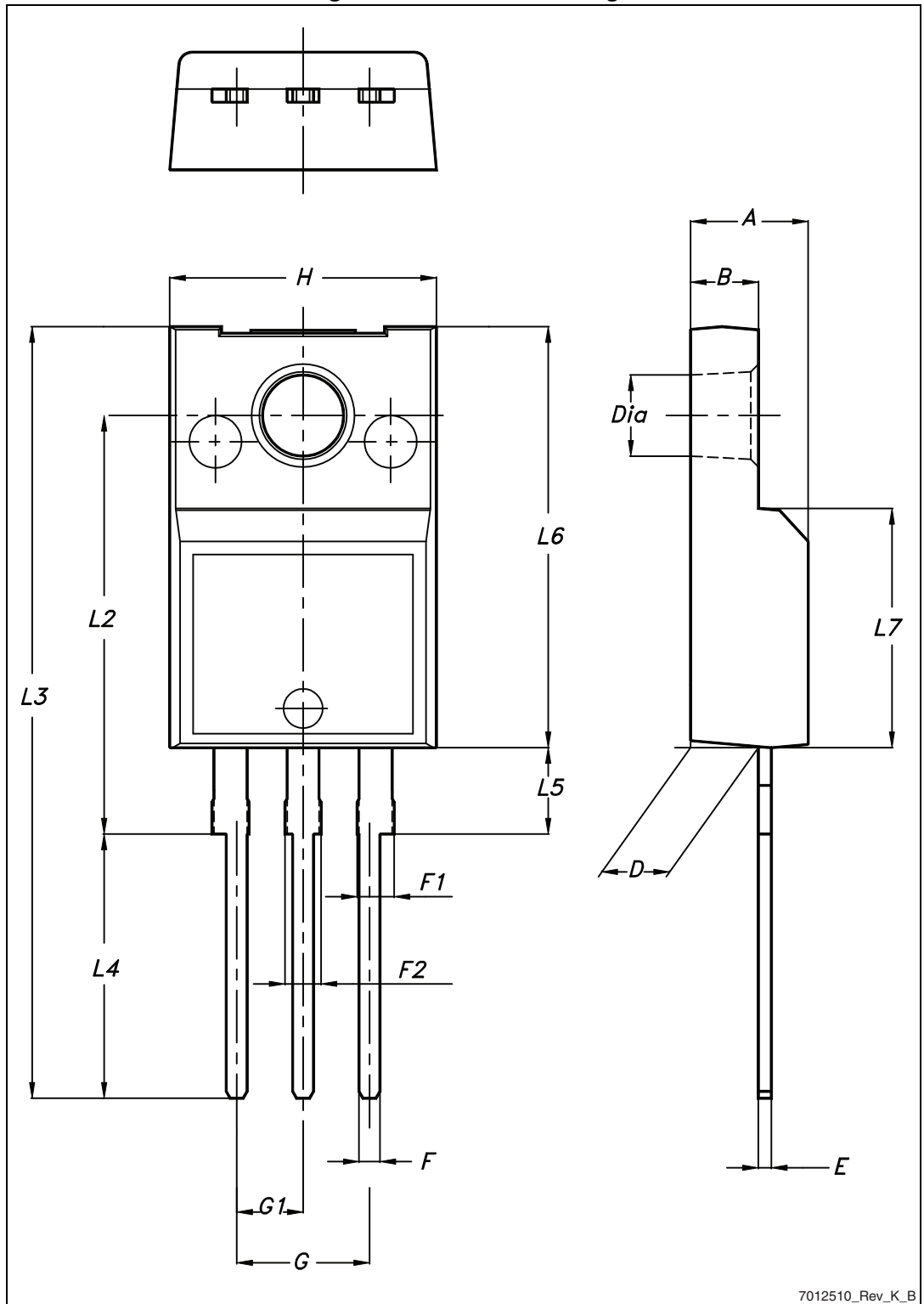


a. All dimensions are in millimeters

Table 10. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 27. TO-220FP drawing



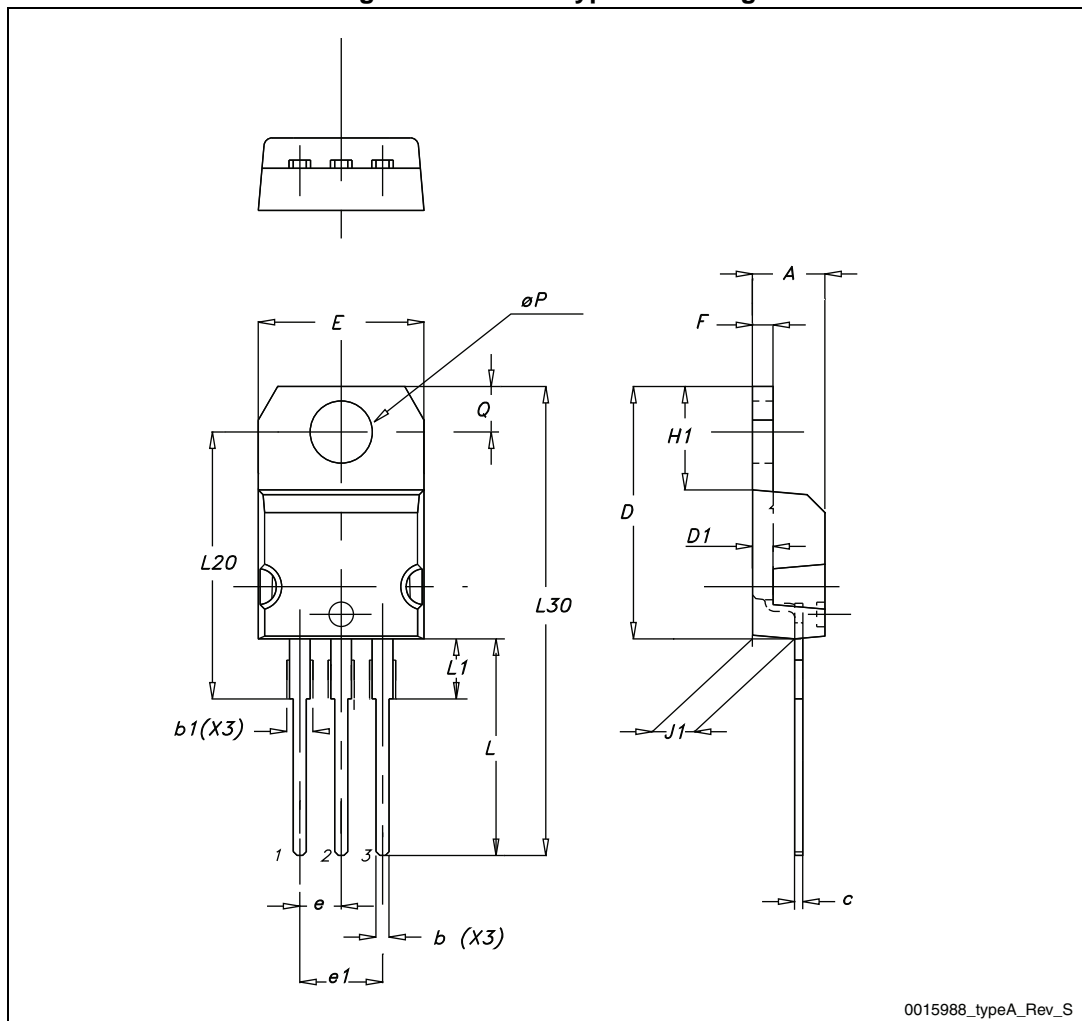
7012510\_Rev\_K\_B

Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



Figure 28. TO-220 type A drawing

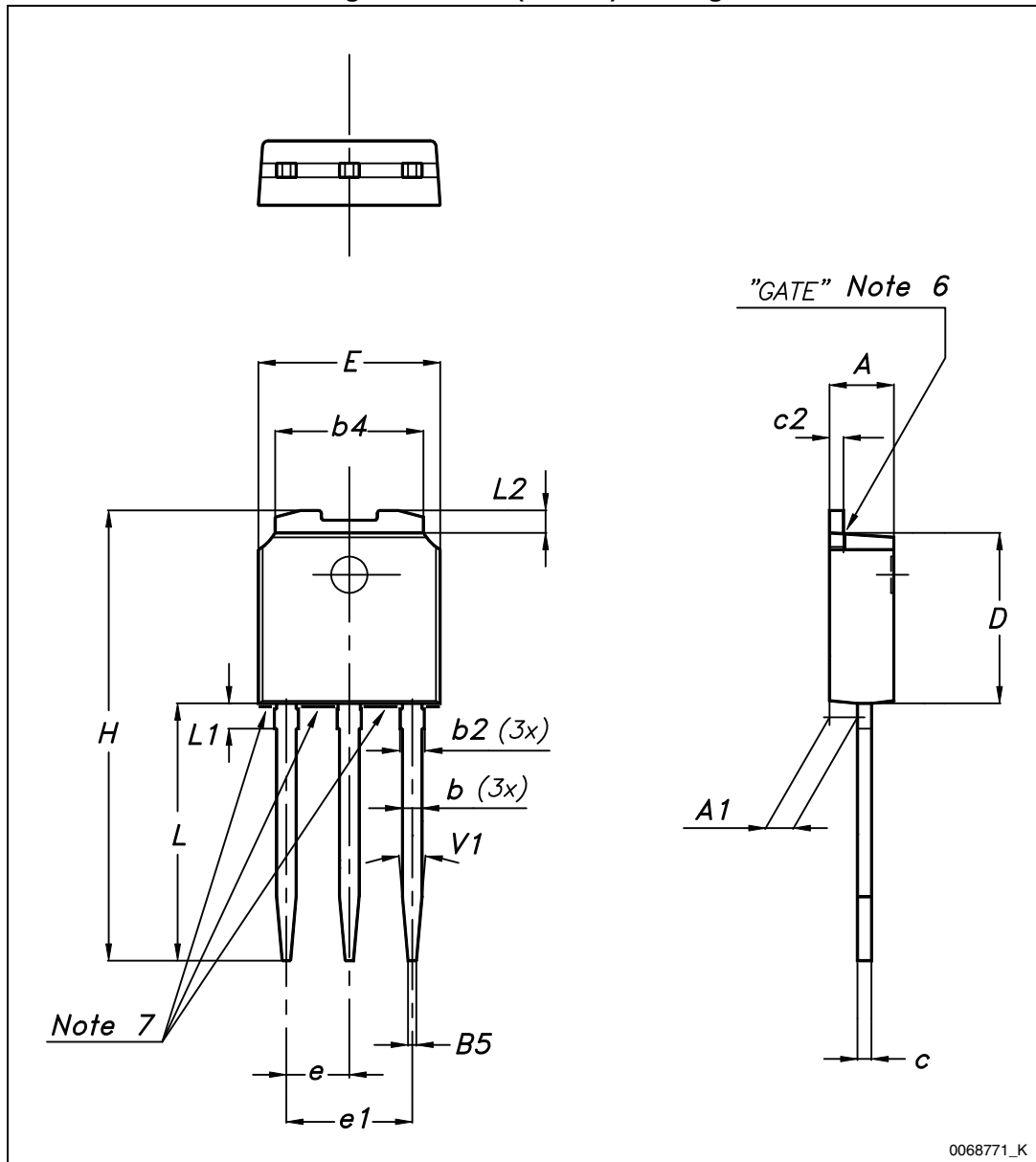


0015988\_typeA\_Rev\_S

Table 12. IPAK (TO-251) mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.35
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.15
E	6.40		6.55
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

Figure 29. IPAK (TO-251) drawing



## 5 Packaging mechanical data

Table 13. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 30. Tape for DPAK (TO-252)

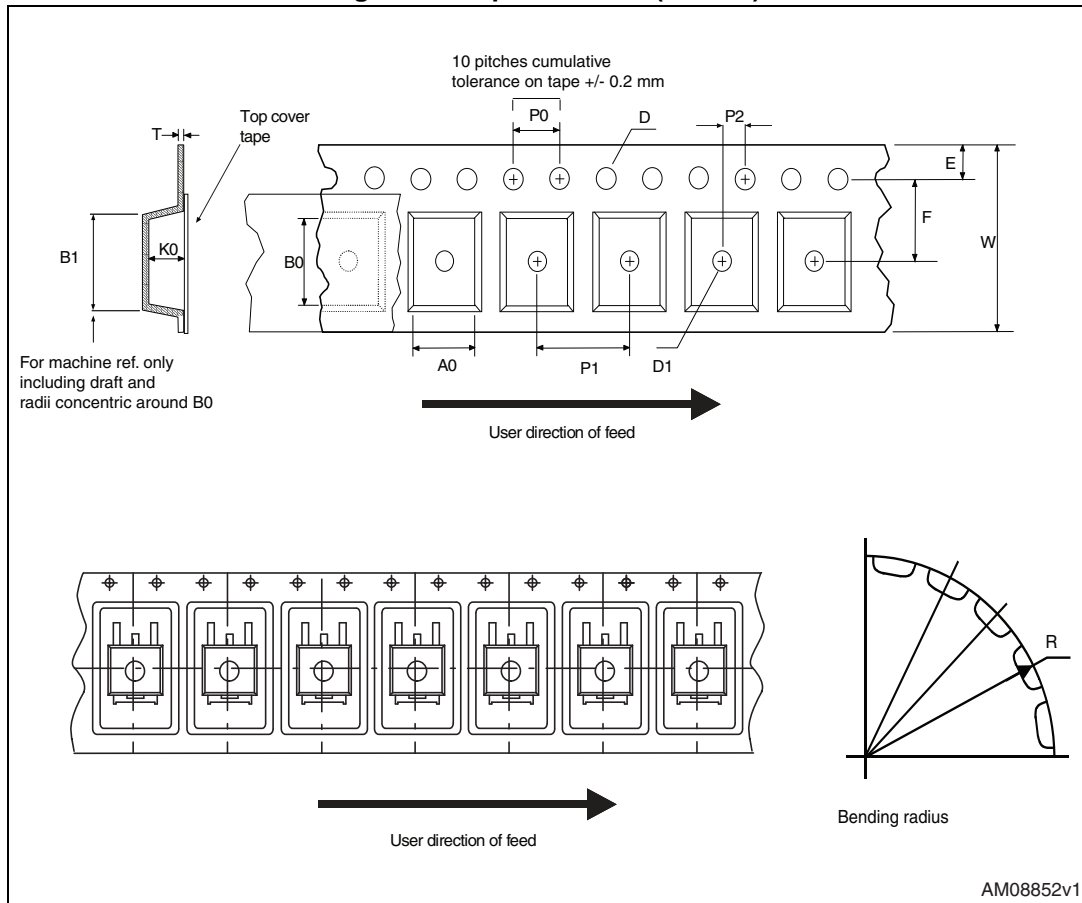
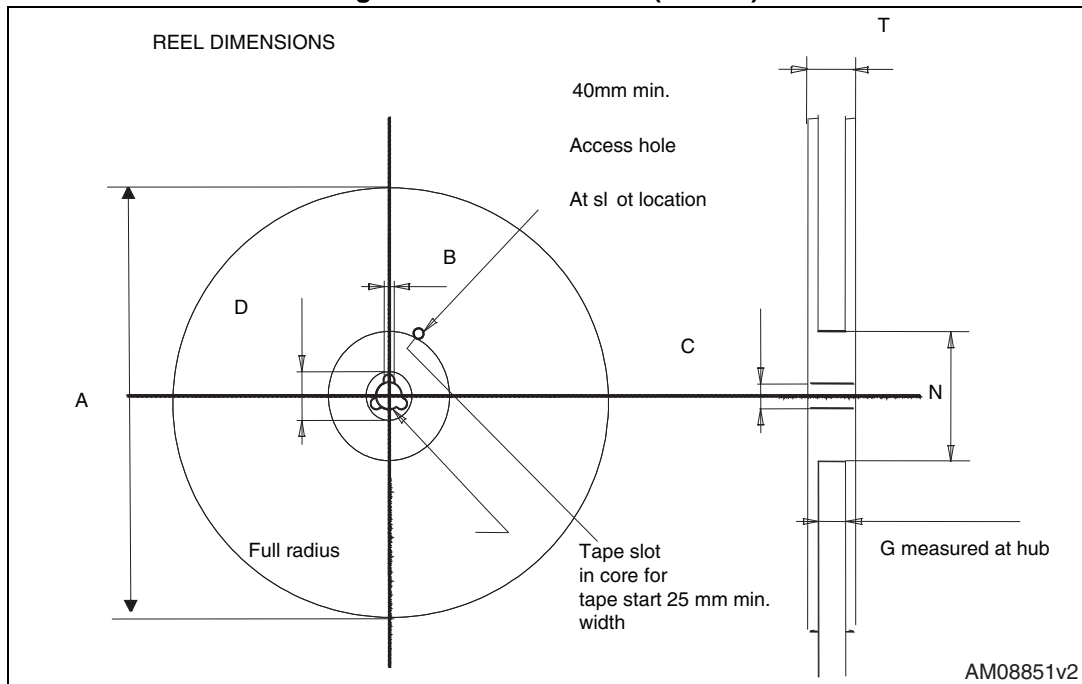


Figure 31. Reel for DPAK (TO-252)



## 6 Revision history

Table 14. Document revision history

Date	Revision	Changes
12-May-2009	1	First release
11-Dec-2009	2	Document status promoted from preliminary data to datasheet
15-May-2013	3	<ul style="list-style-type: none"><li>– Updated: <a href="#">Section 4: Package mechanical data</a></li><li>– Minor text change on the cover page.</li></ul>

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